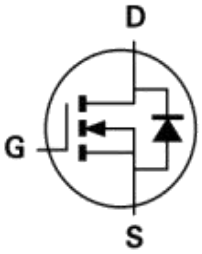
LSC025M65B

SiC N-Channel MOSFET

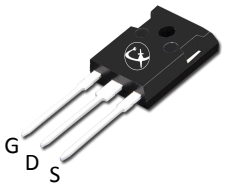
MAIN CHARACTERISTICS

I_D	111A
V_{DS}	800V
Ros(on)-Typ@ Vgs=18V	23mΩ



FEATURES

- High Speed Switching
- High Blocking Voltage with Low RDS(on)
- Easy to Paralle
- Simple to Drive



TO-247

Benefits

- Increased Power Density
- Faster Operating Freequenc
- Reduction of Heat Sink Requirements
- Higher Efficiency
- Reduced EMI

APPLICATIONS

- Power Factor Correction Modules
- Switch Mode Power Supplies
- DC-AC Inverters
- High Voltage DC/DC Converters

Product specification classification

Part Number	Package	Mode Name	Pack
LSC025M65B	TO-247	LSC025M65B	Tube

Maximum Ratings at Tc=25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	800	V
Gate-Source Voltage	V_{GS}	-8/+22	V
Gate-Source Voltage,max.Transient Voltage tp≤0.5μs,D<0.001	V_{GSmax}	-8/+22	V
Recommended Operation Value	VGSop	-4/+18	V
Continue Drain Current Tc=25℃	I_D	111	A
Continue Drain Current Tc=100℃		79	
Pulsed Drain Current	I_{DM}	230	A
Non-Repetitive Avalanche Switching Energy	E_{AS}	1012	mJ
Repetitive Avalanche Energ	E_{AR}	627	mJ
Short-Circuit Withstand Time	t_{SC}	2.5	μs
Power Dissipation TC=25℃	P_D	341	W
Power Dissipation TC=100℃		208	W
Operating Temperature Range	T_J	-40 to +175	°C
Storage Temperature Range	T_{STG}	-40 to +175	°C
Soldering Temperature	Tsold	260	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.44	°C/W
Thermal Resistance, Junction to	$R_{\theta JA}$	26.8	°C/W

Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{GS} = 0 V,I_D = 100μA	BV_{DSS}	800	-	-	V
Drain-Source Leakage Current	VDS = 800V, VGS = 0 V	I_{DSS}	-	1	-	μA
Gate Leakage Current	V_{GS} = 18 V, V_{DS} = 0 V	I_{GSS}	-	-	250	nA
Gate-Source Threshold Voltage	V_{DS} = V_{GS} , I_D = 10 mA TJ = 25℃	$V_{GS(th)}$	2	2.7	4	V
	V_{DS} = V_{GS} , I_D = 10 mA TJ = 175℃		-	2	-	V
Drain-Source On-State Resistance	V_{GS} = 18 V, I_D = 33.5 A TJ = 25℃	$R_{DS(on)}$	-	23	31	mΩ
	V_{GS} = 18 V, I_D = 33.5 A, TJ = 175℃		-	25	-	mΩ
Forward Transconductance	V_{DS}=20V, I_D=33.5A	gfs	-	24	-	S
Internal Gate Resistance	f=1MHz	RG(int)	-	1.6	-	Ω
Input Capacitance	VDS=600V,VGS=0V, f=100KHz	C_{iss}	-	2162	-	pF
Output Capacitance		C_{oss}	-	195	-	pF
Reverse Transfer Capacitance		C_{rss}	-	14	-	pF
Coss Stored Energy		Eoss	-	40	-	μJ
Total Gate Charge(Note2)	I_D =33.5A, V_{DD} =400V, V_{GS} =-4/+ 18 V	Q_G	-	100	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	25	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	28	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current	VGS = -4 V, Tc=25°C	I_S	-	79	-	A
	VGS = -4 V, Tc=100°C		-	45	-	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	230	-	A
Drain-Source Diode Forward Voltage	VGS = -4 V, ISD = 16.8A Tj=25℃	V_{SD}	-	3.8	-	V
	VGS = -4 V, ISD=16.8A Tj=175℃		-	3.4	-	V
	VGS = -4 V, ISD = 33.5 A Tj=25℃		-	4.2	-	V
	VGS = -4 V, ISD=33.5 A Tj=175℃		-	3.9	-	V
Reverse Recovery Time(Note2)	VGS = -4 V，I_{SD} = 33.5 A, V_R =400V, dIF/dt =1862A/μs	trr	-	19	-	ns
Reverse Recovery Charge(Note2)		Qrr	-	230	-	nC
Peak Reverse Recovery Current		Irrm	-	22.2	-	A
Reverse Recovery Time(Note2)	VGS = -4 V，I_{SD} = 33.5A, V_R =400V, dIF/dt =1764A/μs	trr	-	22	-	ns
Reverse Recovery Charge(Note2)		Qrr	-	343	-	nC
Peak Reverse Recovery Current		Irrm	-	27.1	-	A

Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

RATINGS AND CHARACTERISTIC CURVES

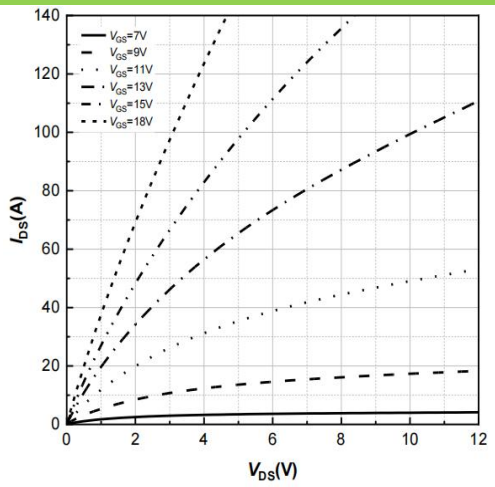


Figure 1. **Output Characteristics T_j=-40°C**

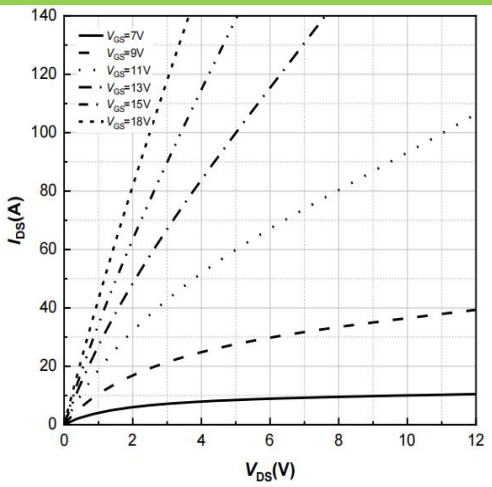


Figure 2. **Output Characteristics T_j=25°C**

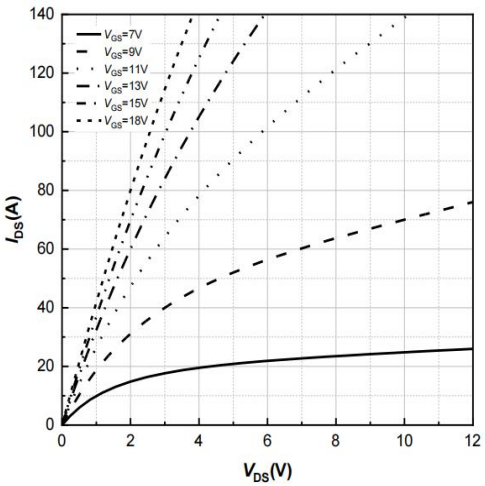


Figure 3. **Output Characteristics T_j=175°C**

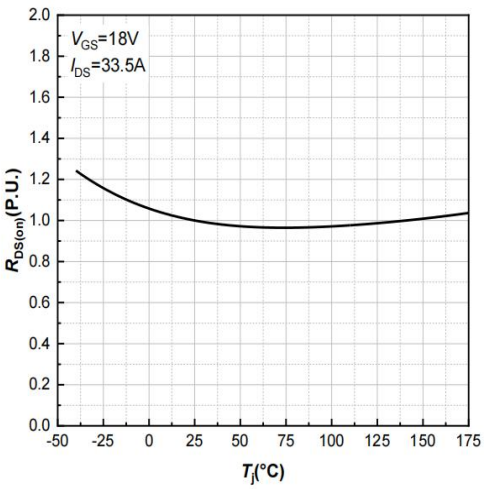


Figure 4. **Normalized On-Resistance vs. Temperature**

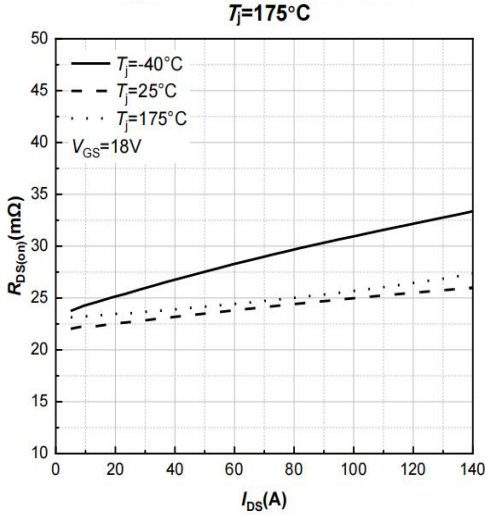


Figure 5. **On-Resistance vs. Drain Current For Various Temperatures**

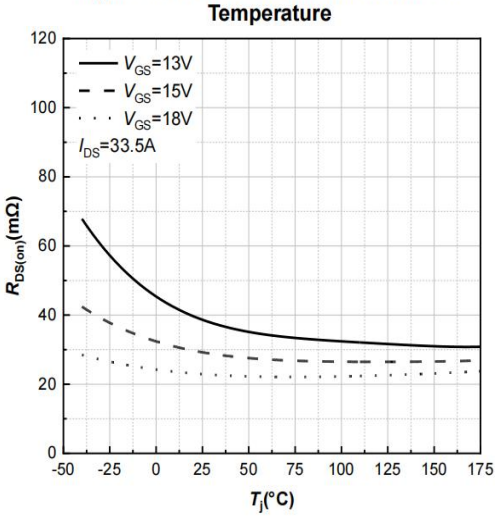


Figure 6. **On-Resistance vs. Temperature For Various Gate Voltage**

RATINGS AND CHARACTERISTIC CURVES

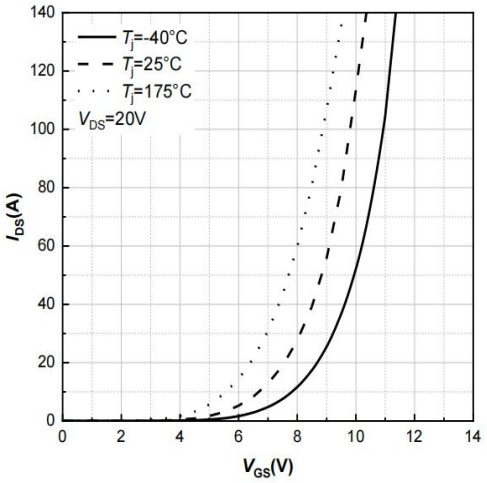


Figure 7. **Transfer Characteristic for Various Junction Temperatures**

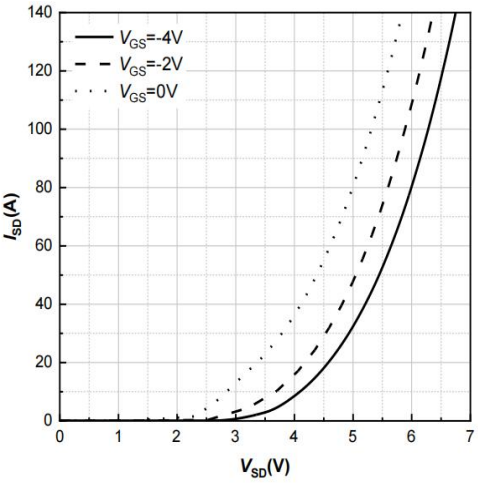


Figure 8. **Body Diode Characteristic T_j=-40°C**

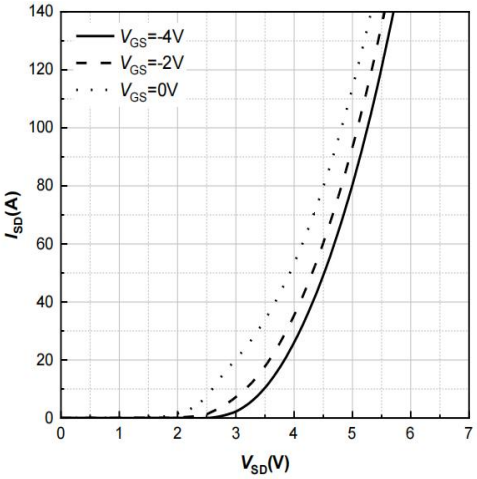


Figure 9. **Body Diode Characteristic T_j=25°C**

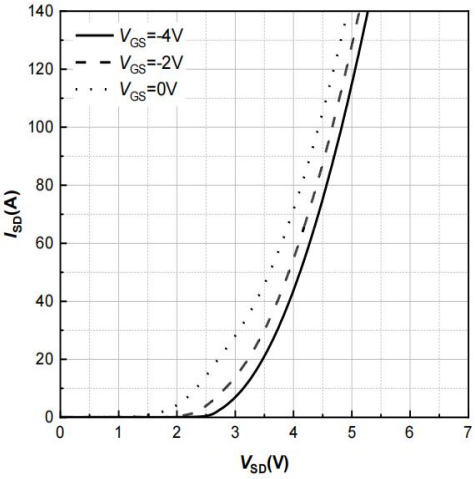


Figure 10. **Body Diode Characteristic T_j=175°C**

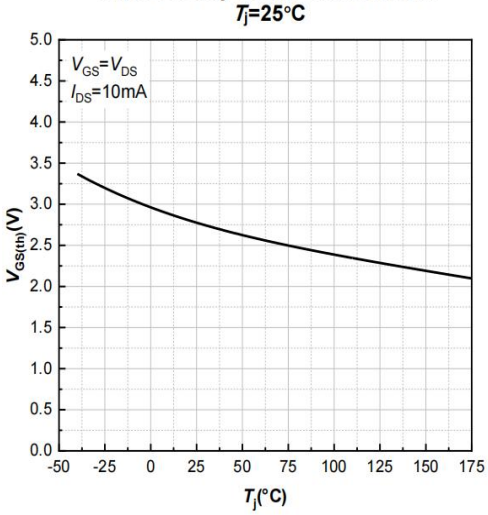


Figure 11. **Threshold Voltage vs. Temperature**

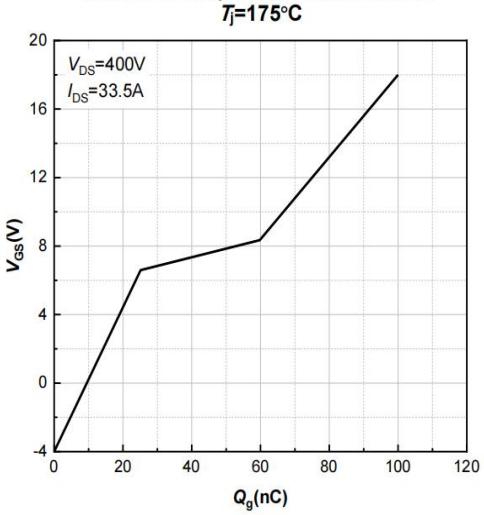


Figure 12. **Gate Charge Characteristics**

RATINGS AND CHARACTERISTIC CURVES

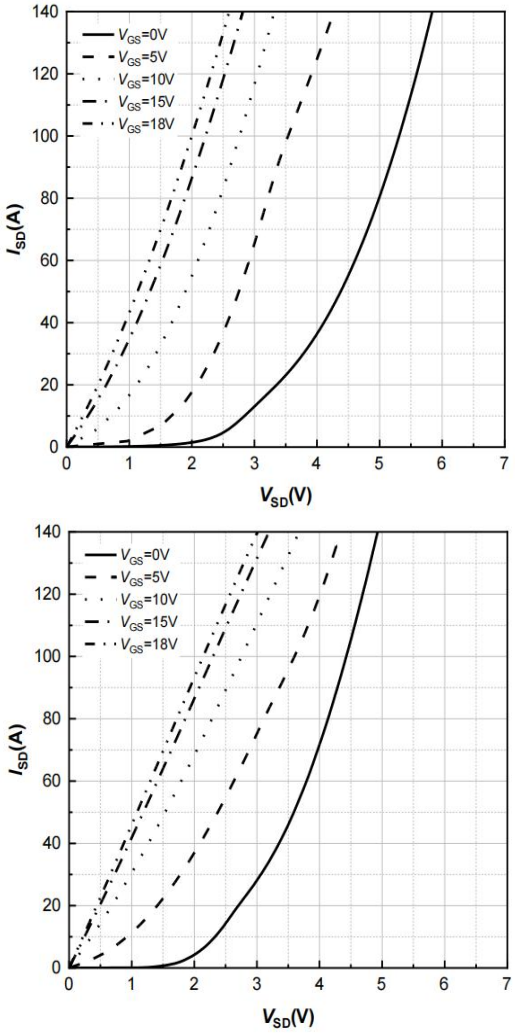


Figure 15. **3rd Quadrant Characteristic T_j=175°C**

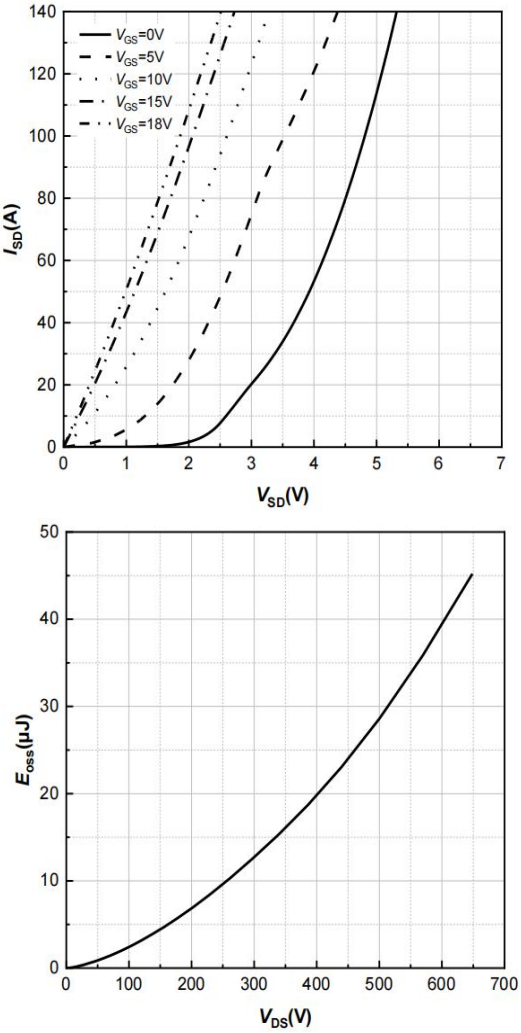


Figure 16. **Output Capacitor Stored Energy**

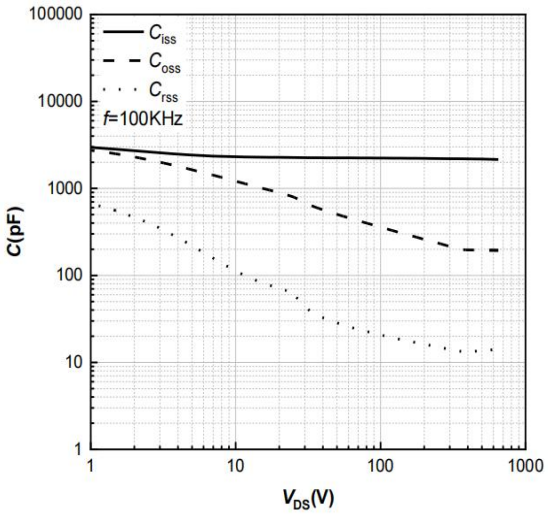


Figure 17. **Capacitances vs. Drain-Source**

Package Outline Dimensions millimeters

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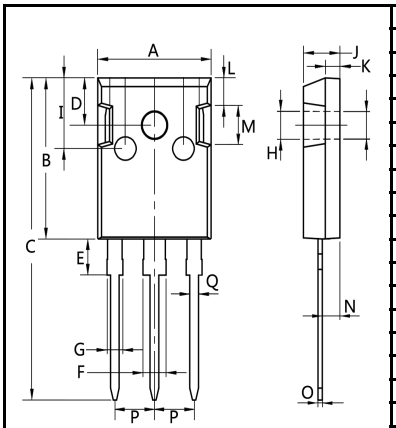
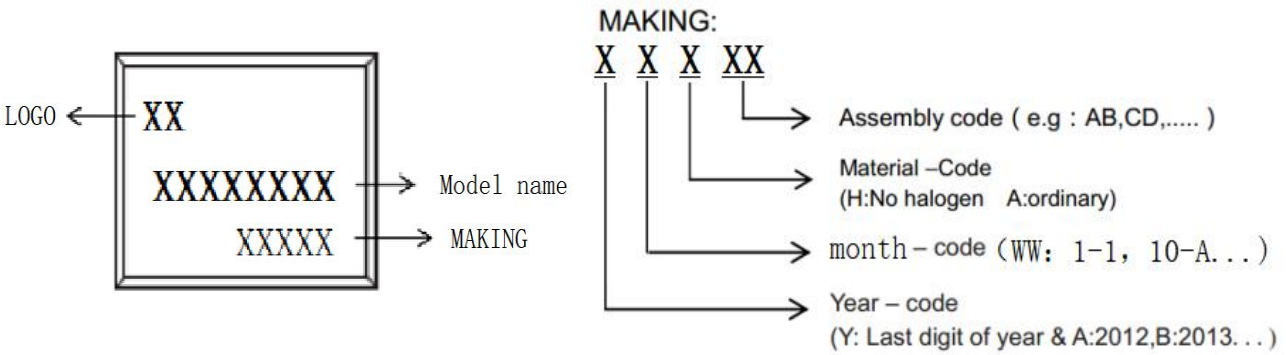
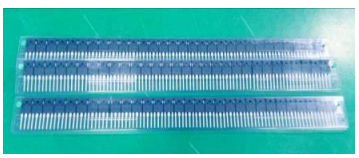


Dim.	Min.	Max.
A	15	16
B	20	21
C	40	42
D	5.5	6.5
E	4	5.5
F	2.5	3.5
G	1.75	2.5
H	3	4
I	8	10
J	4.9	5.1
K	1.9	2.1
L	3	4
M	4.75	5.25
N	2	3
O	0.55	0.65
P	Typ 5.4	
Q	1.17	1.3
All Dimensions in millimeter		
ΦP1	7.19 REF	
All Dimensions in millimeter		

Marking on the body



packing instruction

PKG	Minimal Package	Box	Carton
TO-247			
	30pcs/pdpe	600pcs/box	3000pcs/Carton

Notice

All product,product specifications and data are subject to change without notice to improve.The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying poer exceeding normal rated

poer; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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Revision History

Rev	Changes	Date
2.0	First version	2026/5/27